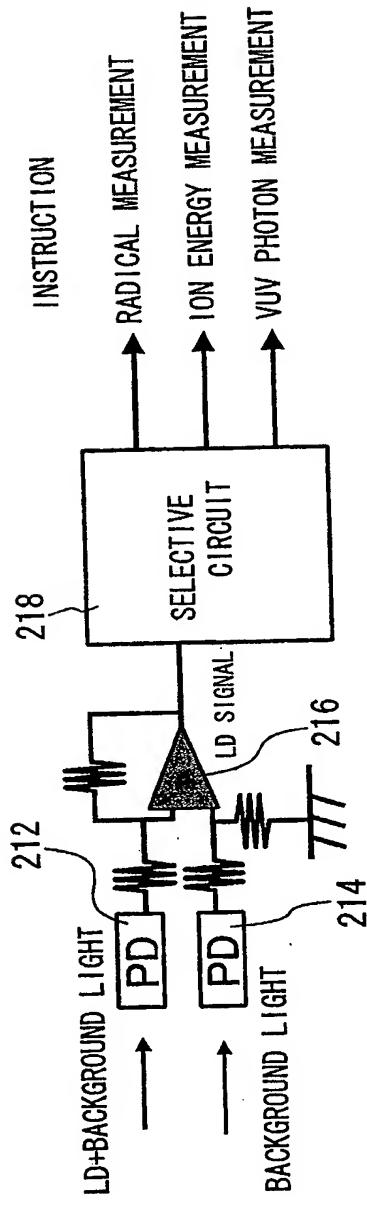


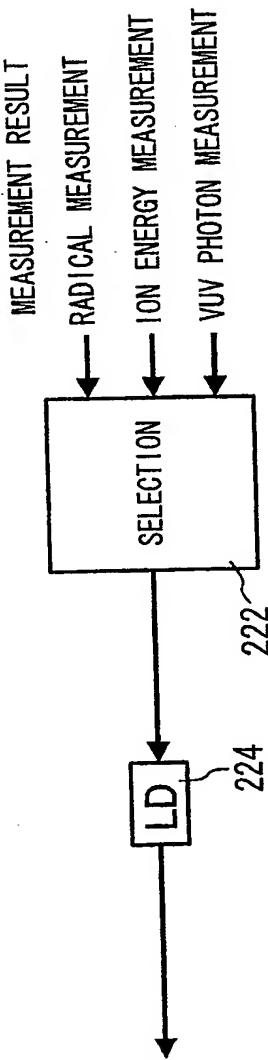


Fig. 4 (a) INPUT



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Fig. 4 (b) OUTPUT



STRUCTURE OF ON-WAFER ION ENERGY ANALYZER

Fig. 7 (a)

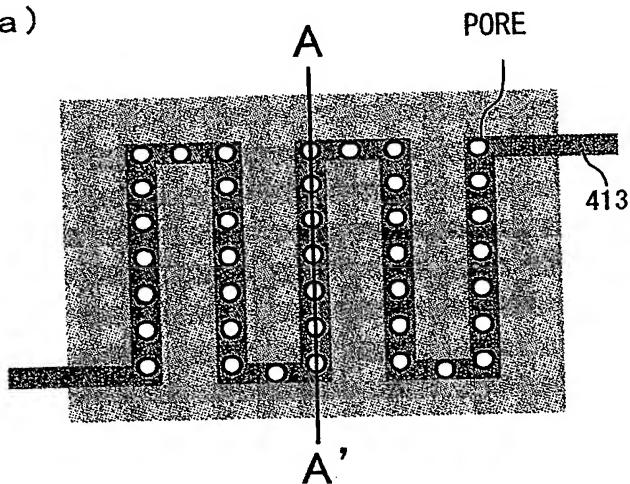


Fig. 7 (b)

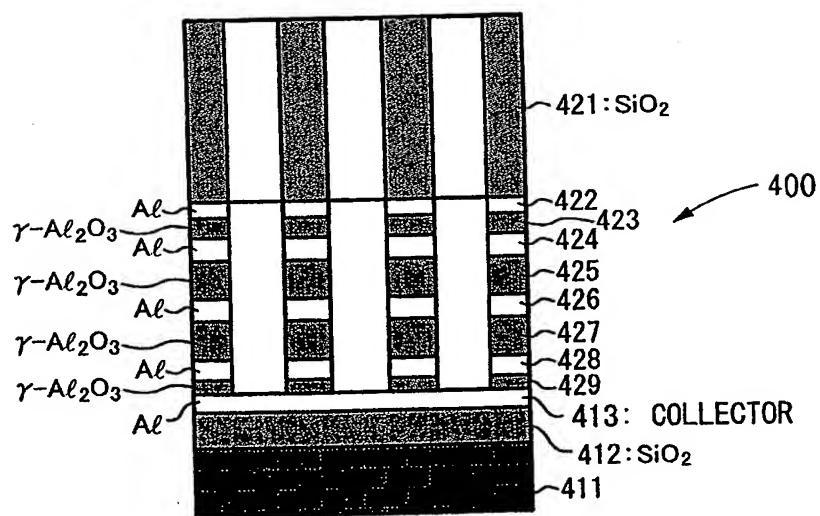
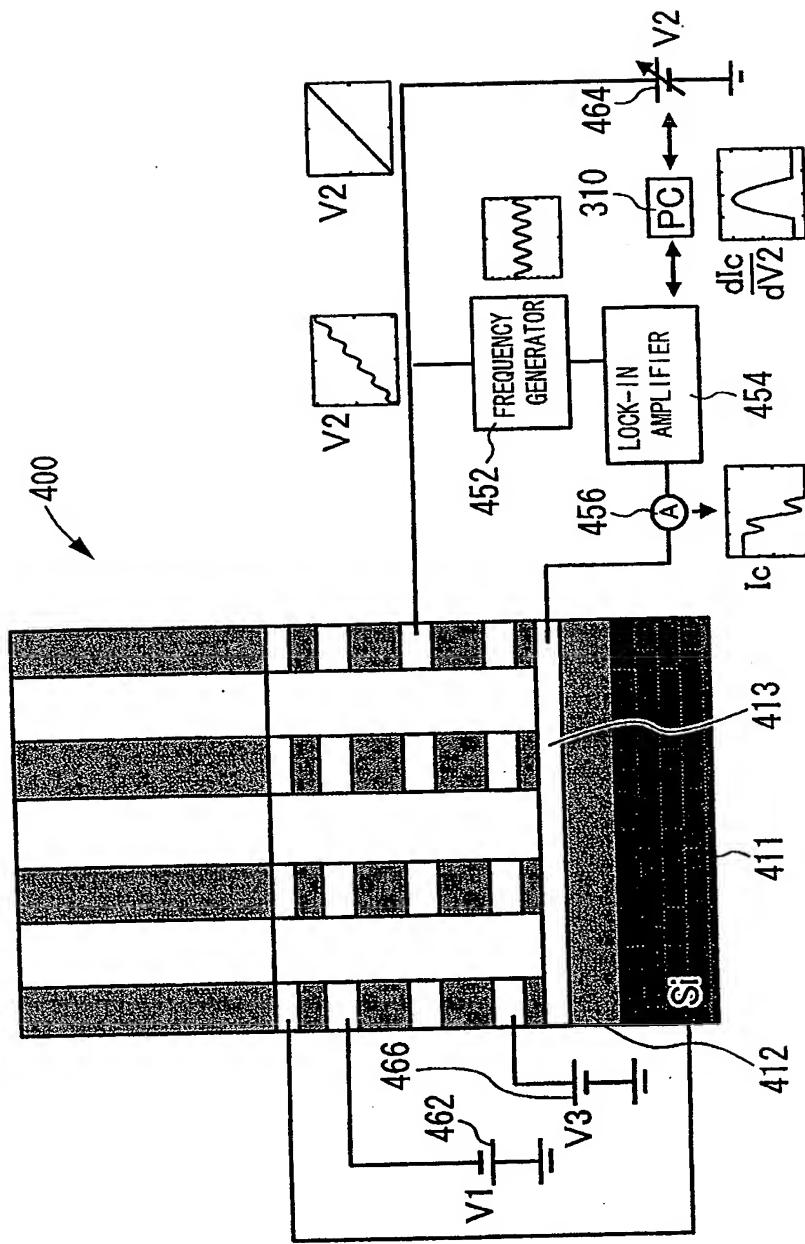


Fig. 8 MEASUREMENT SYSTEM OF ON-WAFER ION ENERGY ANALYZER



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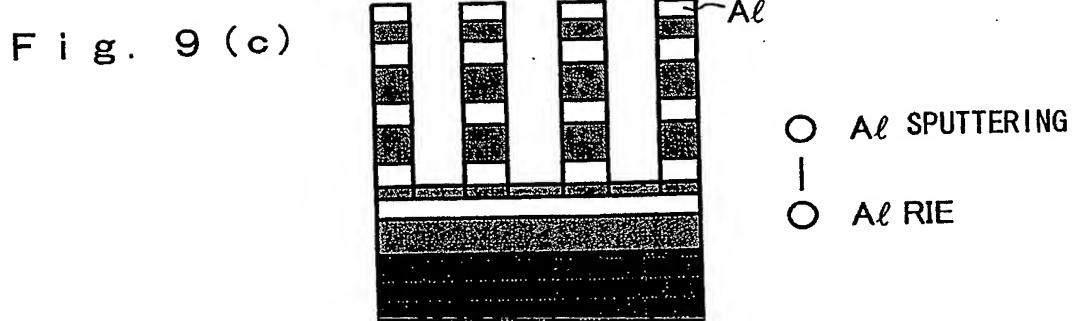
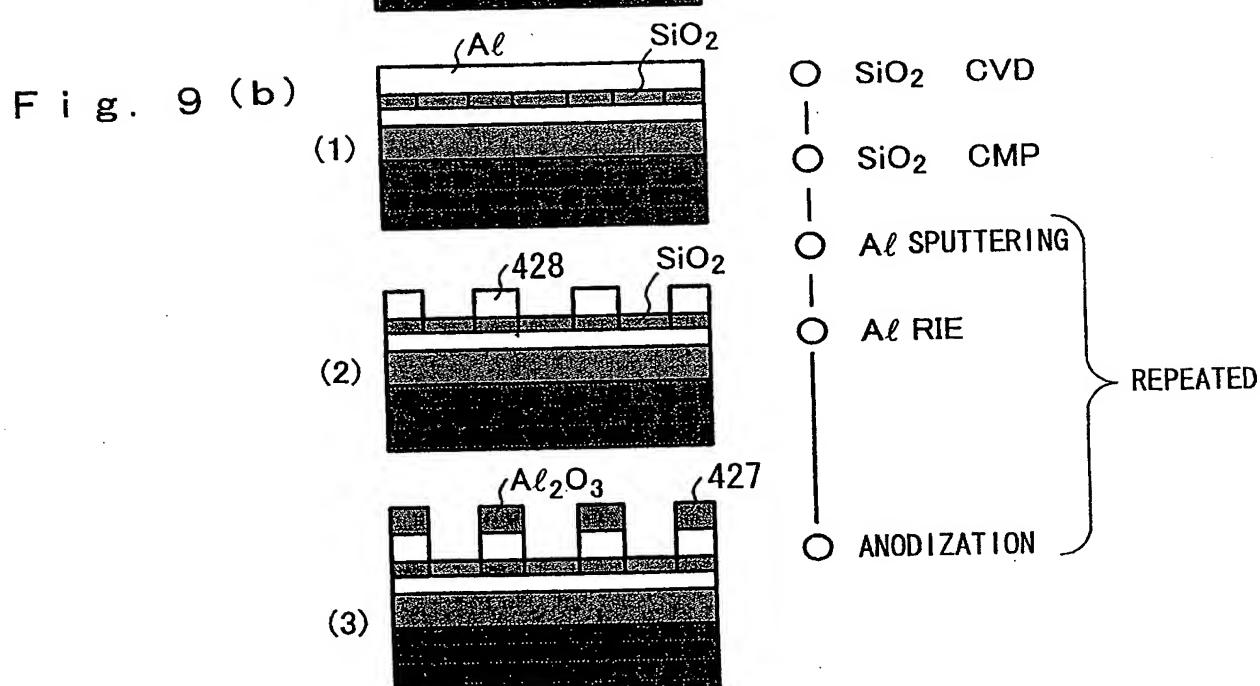
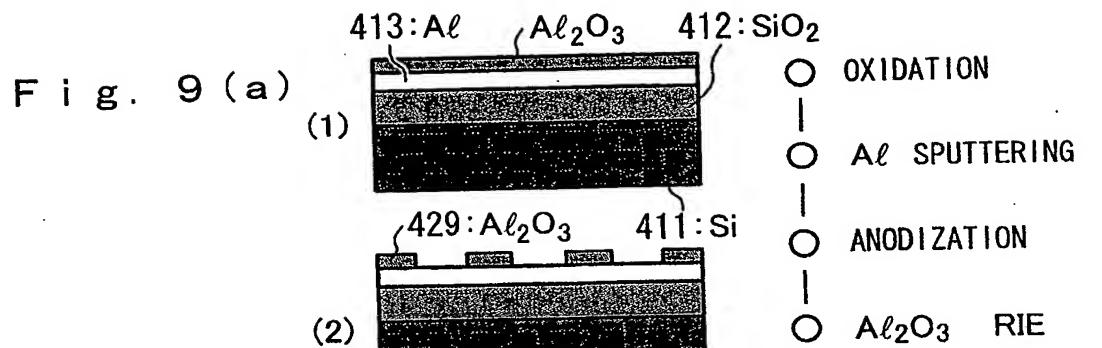
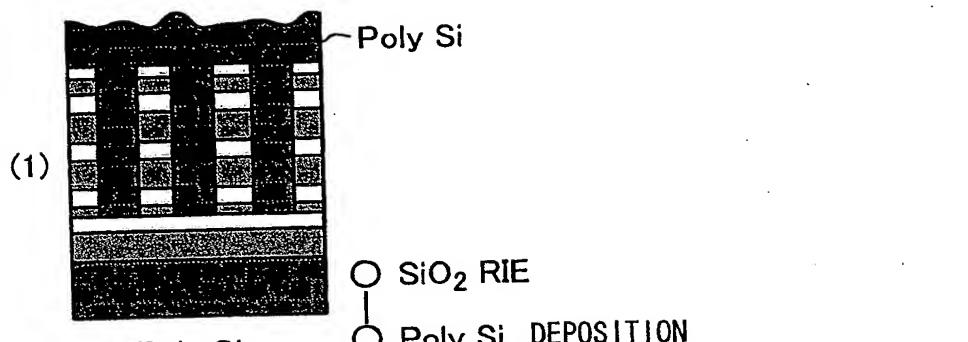


Fig. 10(d)



(2)

Fig. 9(e)

○ SiO<sub>2</sub> DEPOSITION  
○ SiO<sub>2</sub> RIE

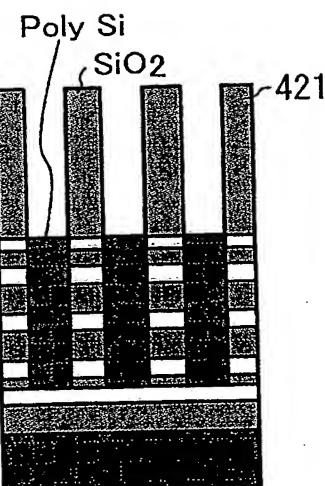
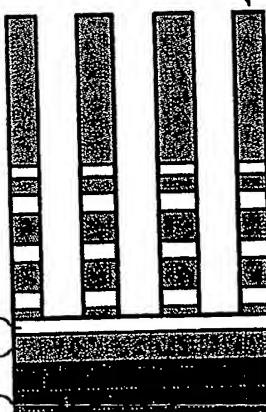


Fig. 9(f)

○ Poly RIE

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412  
411



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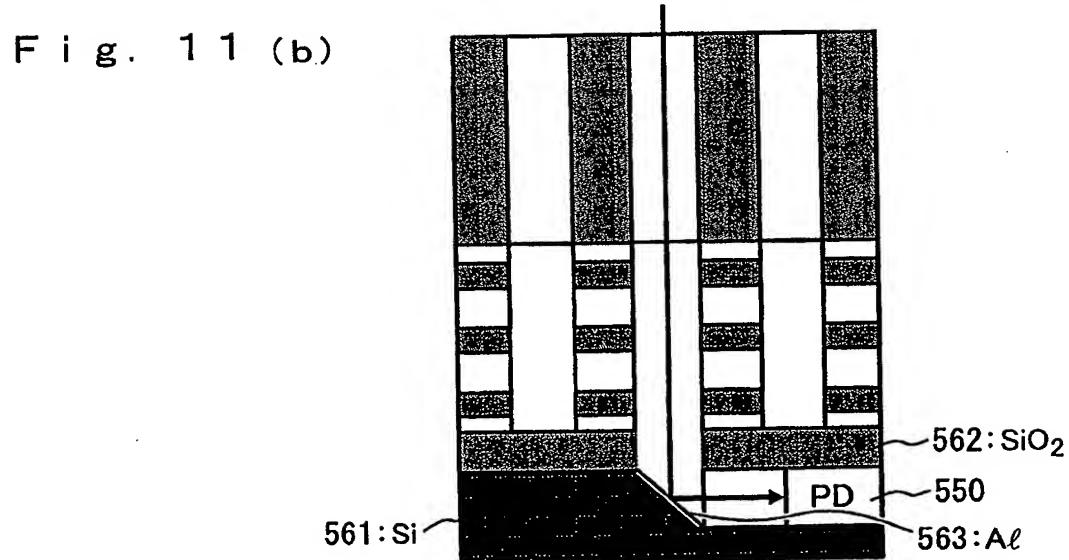
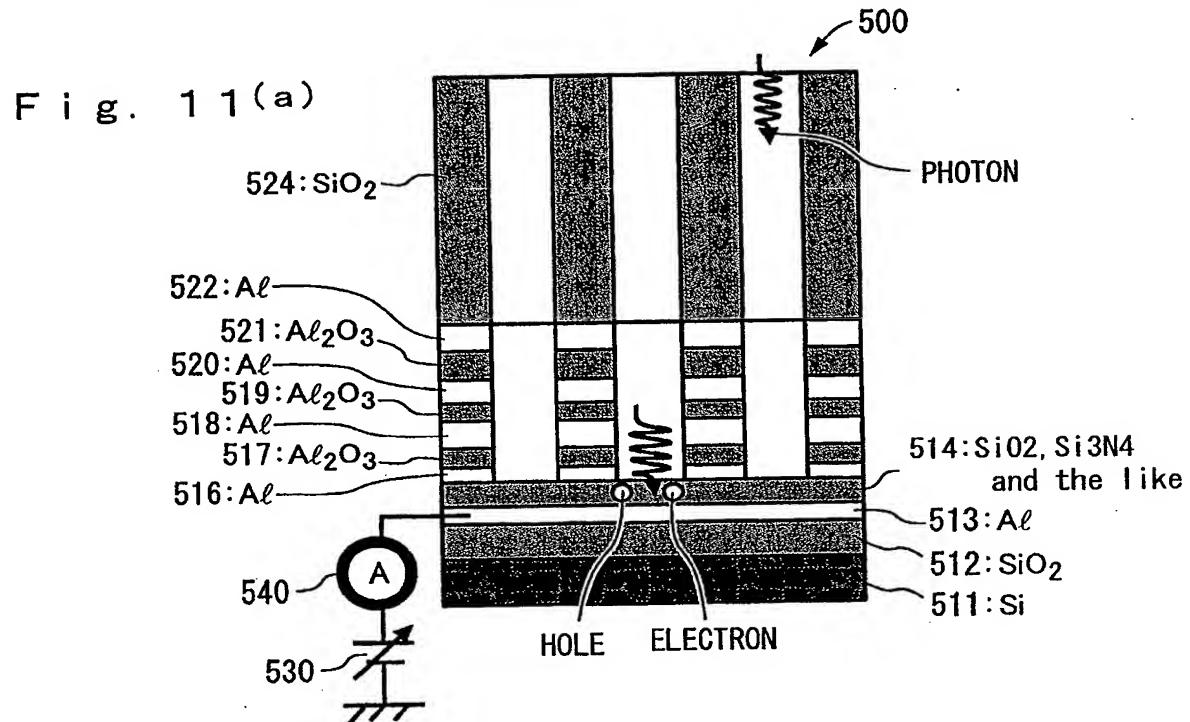


Fig. 14 (a)

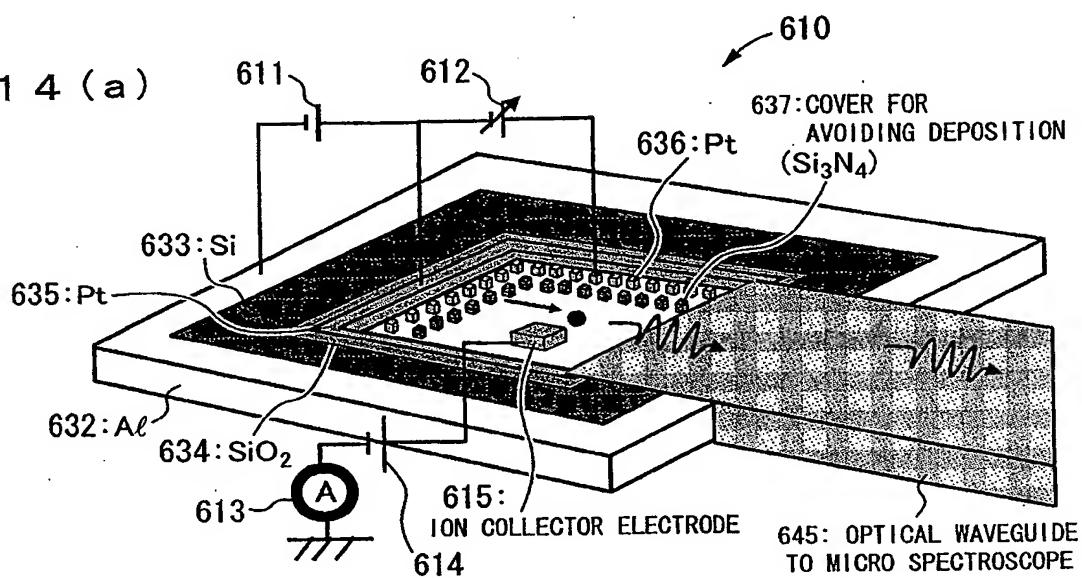


Fig. 14 (b)

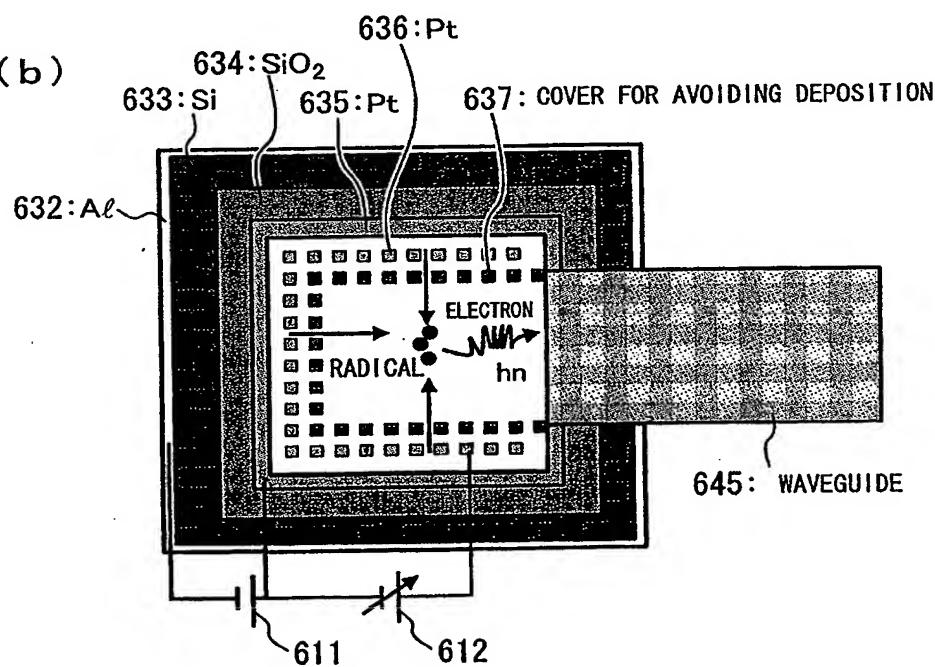


Fig. 15

MICRO SPECTROSCOPE

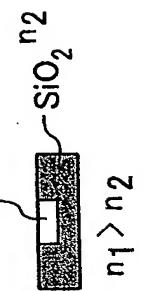
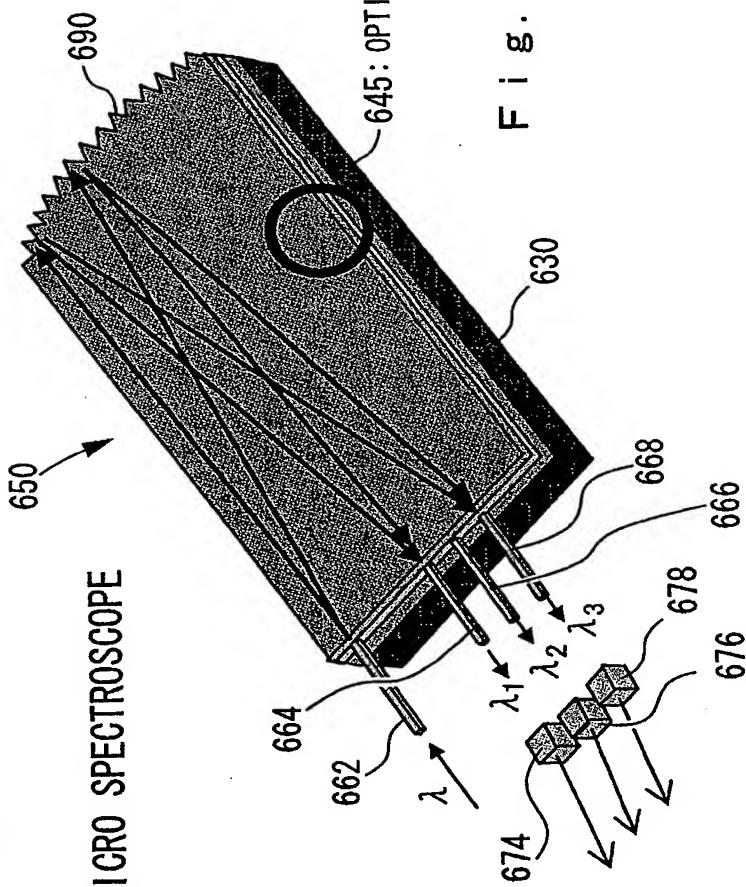


Fig. 15 (a)

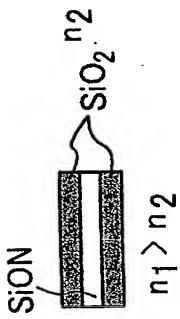


Fig. 15 (b)

MANUFACTURING PROCESS OF MICRO ION RADICAL ANALYZER(1)

Fig. 16(a) OXIDATION



Fig. 16(b) Si DEPOSITION, ETCHING

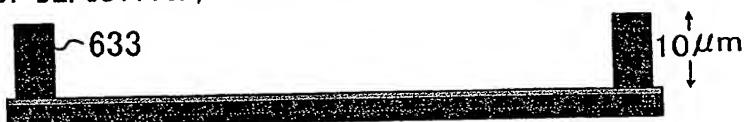


Fig. 16(c) Al VAPOR DEPOSITION, ETCHING



Fig. 16(d) SiO<sub>2</sub> DEPOSITION, ETCHING



Fig. 16(e) Pt DEPOSITION, PATTERNING

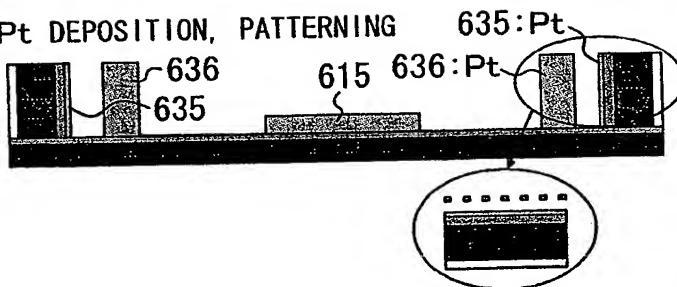
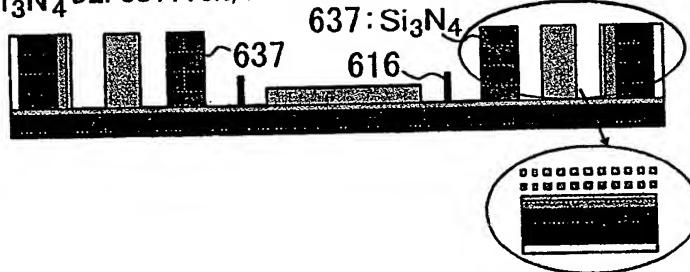


Fig. 16(f) Si<sub>3</sub>N<sub>4</sub> DEPOSITION, ETCHING



MANUFACTURING PROCESS OF MICRO ION RADICAL ANALYZER(2)

Fig. 17(g) SiO<sub>2</sub> DEPOSITION, ETCHING

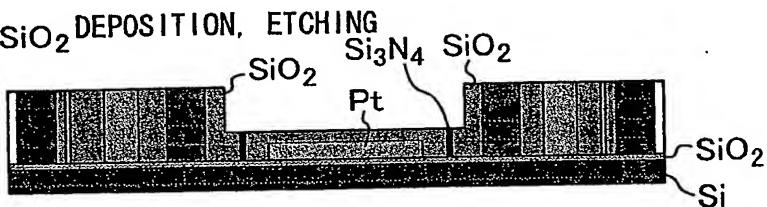


Fig. 17(h) Si<sub>3</sub>N<sub>4</sub> DEPOSITION, ETCHING

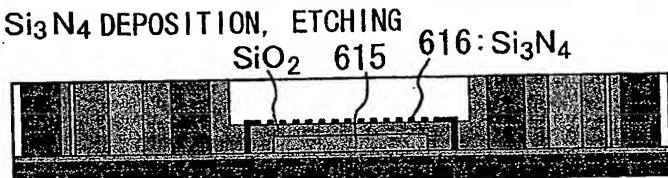
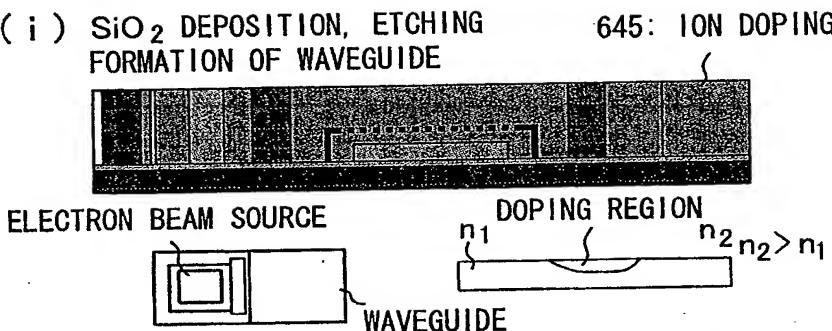


Fig. 17(i) SiO<sub>2</sub> DEPOSITION, ETCHING  
FORMATION OF WAVEGUIDE



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Fig. 17(j) Si<sub>3</sub>N<sub>4</sub>,Si DEPOSITION

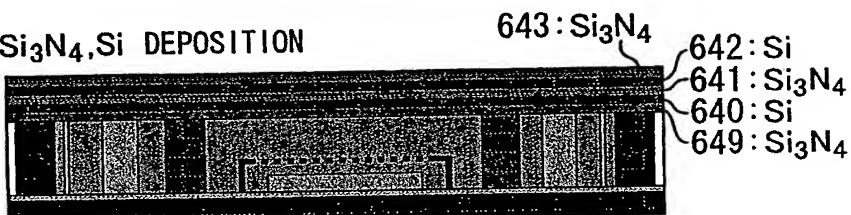


Fig. 17(k) Si<sub>3</sub>N<sub>4</sub>,Si ETCHING  
SiO<sub>2</sub> SACRIFICE LAYER ETCHING

